

Amplifiers Notebook Dr. Ra'ed Al-zoubie

By . Lara Abu Soufa

بأفكارنا نبدع

Review:

n-type : concentration of electrons > concentration of holes

p-type : holes > electrons

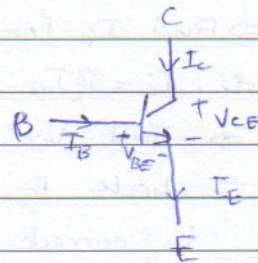
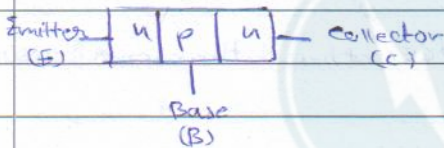
⇒ we can use process to get these materials.

⇒ Transistor : → Bipolar Junction transistor (BJT).

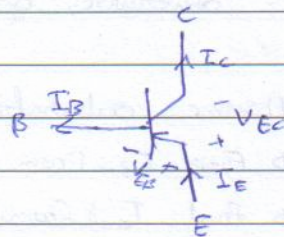
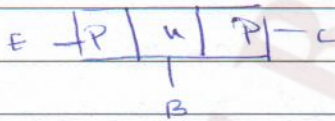
↳ Field Effect transistor (FET).

⇒ BJT

: npn



pnp:



* Modes of operation for BJT :-

① Forward active mode

B-E Forward-biased

B-C Reverse-biased

App: Amplifier.

$$\Rightarrow V_{BE} = V_{BE(ON)} \approx 0.7 \text{ V}$$

$$I_C = \beta I_B$$

$$V_{CE} > V_{CE(sat)} \approx (0.2 - 0.3)$$

② Saturation mode :-

B-E F.W

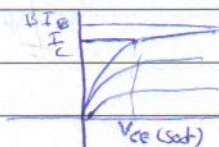
B-C F.W

App: Switch

$$\Rightarrow V_{BE} = V_{BE(ON)} = 0.7 \text{ V}$$

$$I_C < \beta I_B$$

$$V_{CE} = V_{CE(sat)} = 0.2$$



No.

$$50 \leq \beta \leq 200$$

$$\alpha = \frac{\beta}{1+\beta} \approx 0.99$$

④ Inverse active Mode:

B-E Reverse-biased.

B-C Forward-biased.

$$I_C = \beta I_B \rightarrow \text{Forward}$$

$$I_E = I_C + I_B = \beta I_B + I_B$$

$$I_E = (1 + \beta) I_B$$

$$I_C = \frac{1 + \beta}{\beta} I_E \quad I_C = \frac{I_E}{\alpha}$$

How to find the Mode operation:

① Assume forward active mode

⇒ Find I_B from input loop.

$$\Rightarrow I_C = \beta I_B$$

⇒ Find V_{CE} from output loop.

⇒ check if $I_B > 0$ and $V_{CE} > V_{CE(sat)}$, then our assumption is correct.

otherwise, go to step ②.

② Assume saturation Mode:

⇒ Find I_B from input loop.

⇒ Find I_C from output loop

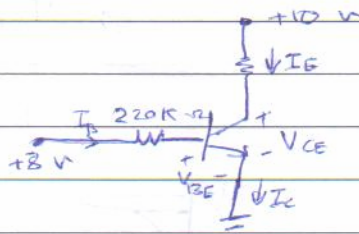
using $V_{CE} = V_{CE(sat)}$

to check if $I_C < I_B \beta$, then our assumption is correct.

otherwise, the mode of the operations is cutoff.

Example 1: Find the Mode operation in this ckt:

(Given: $V_{CE(sat)} = 0.2 \text{ V}$, $\beta = 100$, $V_{BE(on)} = 0.7 \text{ V}$.)



power	pc	ac+dc	ac
I_B	I_B	i_B	i_b
			No.

⇒ Assume F.W

→ input loop:

$$-8 + 220 I_B + 0.7 = 0$$

$$I_B = \frac{8 - 0.7}{220} = 33.2 \text{ } \mu\text{A}$$

$$I_C = \beta I_B = 3.32 \text{ mA}$$

→ output loop:

$$-10 + 4 I_C + V_{CE} = 0$$

$$V_{CE} = 10 - 4 I_C = -3.28 \text{ V}$$

⇒ since $V_{CE} < V_{CE(sat)}$ \Rightarrow then our assumption is incorrect.

⇒ Assume Saturation Mode:

→ input loop:

$$I_B = 33.2 \text{ } \mu\text{A}$$

→ output loop:

$$-10 + 4 I_C + 0.2 = 0$$

$$I_C = 2.45 \text{ mA}$$

⇒ check $I_C < \beta I_B$ Yes \Rightarrow saturation mode

(we can't use it as amplifier).

(Quiescent point/operation point)

[b] Find the Q-point values:

$$I_{BQ} = 33.2 \text{ } \mu\text{A}$$

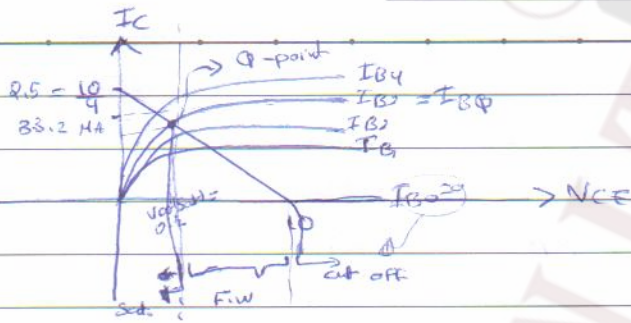
$$I_{CQ} = 2.45 \text{ mA}$$

$$V_{CEQ} = 0.2 \text{ V}$$

[c] Find the DC load line (I_C vs V_{CE}) ?

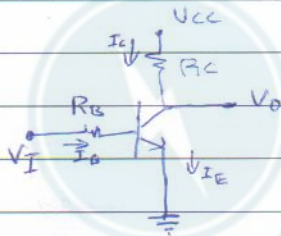
$$-10 + 4 I_C + V_{CE} = 0$$

$$I_C = \frac{10}{4} - \frac{V_{CE}}{4}$$



* The Transistor should be in the forward active mode to work as amplifier, why?

ANS:-



Draw the relationship between V_o & V_i :-

→ Cutoff :

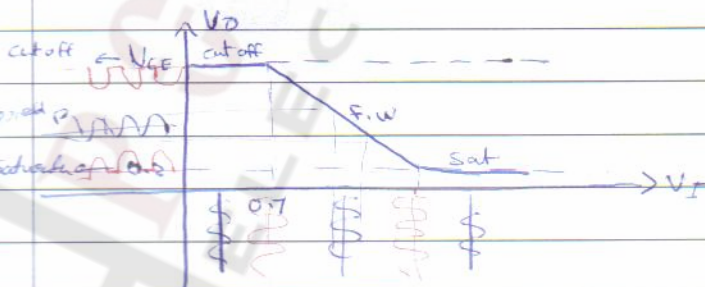
$$I_B = I_C = I_E = 0 \text{ A}$$

$$\text{So, } V_o = V_{CC}$$

⇒ Saturation :

$$V_{CE} = V_{CE}(\text{sat}) = 0.2 \text{ V}$$

$$\text{So, } V_o = V_{CE}(\text{sat}) = 0.2 \text{ V}$$



→ input loop =

$$-V_i + I_B R_B + 0.7 = 0$$

$$I_B = \frac{V_i - 0.7}{R_B}$$

No. _____

$$I_C = \beta I_B = \beta \frac{(V_I - 0.7)}{R_B}$$

→ output loop:-

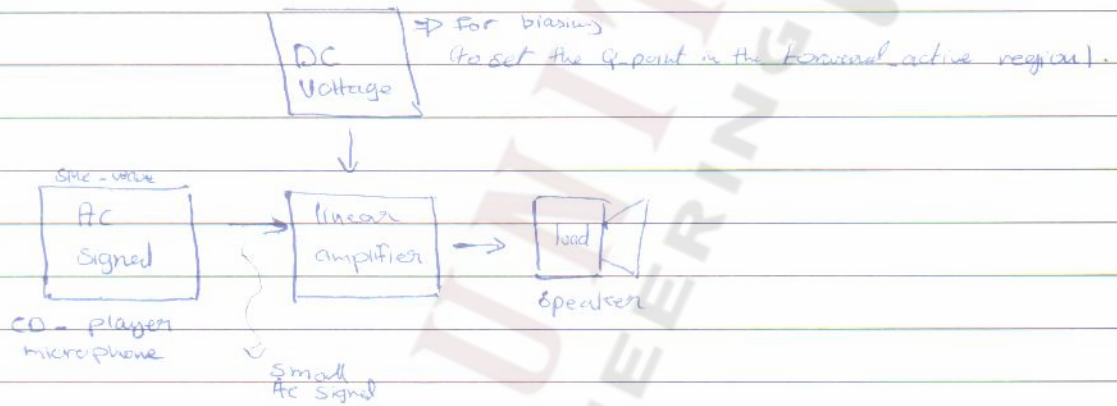
$$-V_{CC} + I_C R_C + V_o = 0$$

\downarrow
 $\beta (V_I - 0.7)$
 R_B

$$-V_{CC} + \frac{\beta R_C}{R_B} (V_I - 0.7) + V_o = 0$$

$$V_o = V_{CC} - \frac{\beta R_C}{R_B} (0.7) + \frac{\beta R_C}{R_B} V_I$$

* Basic BJT Amplifier :



\Rightarrow Linear Amplifier : $V_o = \text{constant} \times V_i$
 \downarrow
 Gain

\rightarrow why? to get a clear amplification.

\Rightarrow Linear circuits : all its components are linear.

\rightarrow linear elements $\rightarrow V \propto I$ is linear.

\parallel \rightarrow linear

∇ \rightarrow non linear

∇ \rightarrow non linear

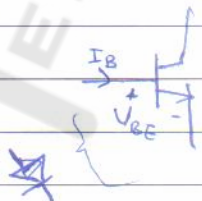
but, amplifier circuit uses transistor. which is not linear element.

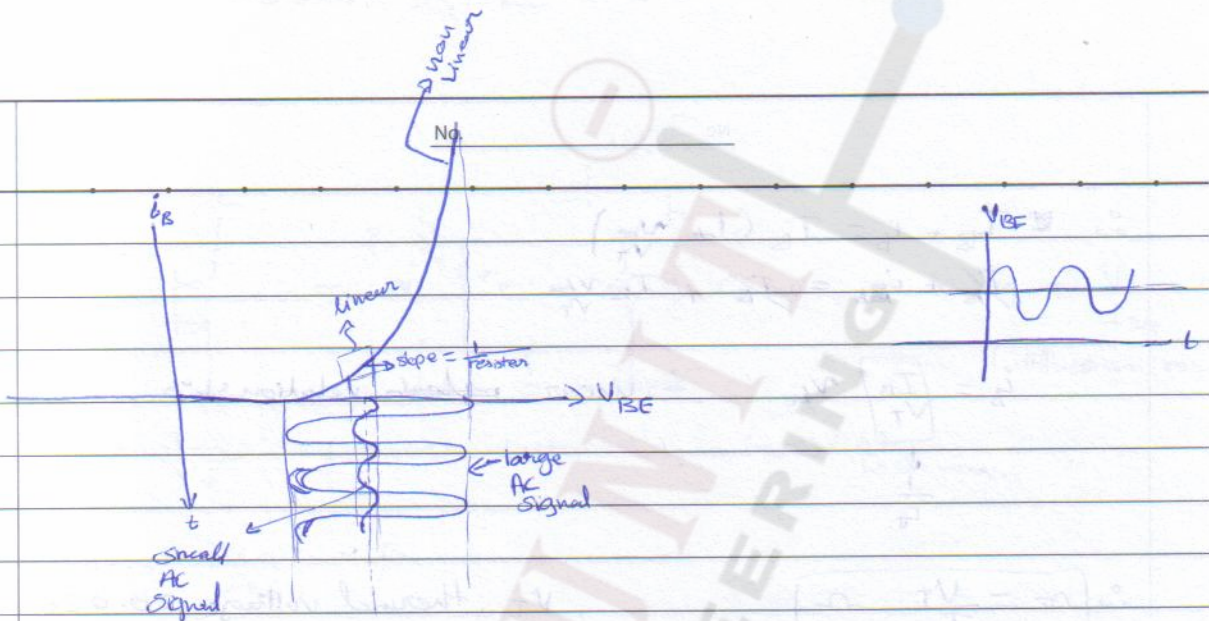
\Rightarrow So we need a solution to get a linear amplifier.

\Rightarrow Solution for small AC signals.

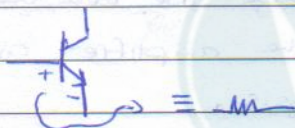
\Rightarrow Transistor will act as a linear device at small AC signals, why?

answer :- Graphically :-





At small AC signal :-



So, at small AC signal the junction B-E is represented by a resistor called r_{π} .

Mathematically :-

$$I_B = I_S \frac{e^{\frac{V_{BE}}{V_T}}}{1+\beta} \quad (\text{From electronics 1})$$

$$I_B + i_b = \frac{I_S}{1+\beta} e^{\frac{V_{BE} + v_{be}}{V_T}} \quad \text{activation current}$$

$$I_B + i_b = \frac{I_S}{1+\beta} e^{\frac{V_{BE}}{V_T}} \cdot e^{\frac{v_{be}}{V_T}}$$

$$I_B + i_b = I_B \cdot e^{\frac{v_{be}}{V_T}}$$

* Taylor series : $e^{\theta} = 1 + \frac{\theta}{1!} + \frac{\theta^2}{2!} + \frac{\theta^3}{3!} + \dots$

IF $\theta \ll 1 \Rightarrow e^{\theta} \approx 1 + \theta$

So, IF $\frac{v_{be}}{V_T} \ll 1 \Rightarrow \frac{v_{be}}{V_T} < 1 \Rightarrow v_{be} < V_T$

then $e^{\frac{v_{be}}{V_T}} \approx 1 + \frac{v_{be}}{V_T}$

$$\therefore I_B + i_b = I_B \left(1 + \frac{v_{be}}{V_T}\right)$$

$$\frac{i_b}{I_B} + \frac{i_{BB}}{I_B} = \frac{I_B}{I_B} + I_B \frac{v_{be}}{V_T}$$

$$i_b = \boxed{\frac{I_B}{V_T}} v_{be} \Rightarrow \text{linear relationship.}$$

↓
 $\frac{1}{r_{\pi}}$

$$\therefore \boxed{r_{\pi} = \frac{V_T}{I_B} \Omega}$$

V_T thermal voltage = 0.026 V

at room temperature
(300 K).

⇒ since we have a linear amplifier, then we can simply apply super position to analyze the amplifier circuit by doing AC then DC analysis.

⇒ To analyze an amplifier circuit :-

Step 1. DC analysis.

① Draw the DC equivalent ckt

→ Kill all the sources

→ replace all capacitor by open ckt.

② Find I_B , I_C , V_{ce}

input loop

βI_B

output loop

Step 2. AC analysis.

① Draw the AC equivalent ckt.

→ Kill all DC sources.

→ replace all capacitor by short ckt.

→ replace the transistor by its small AC-signal

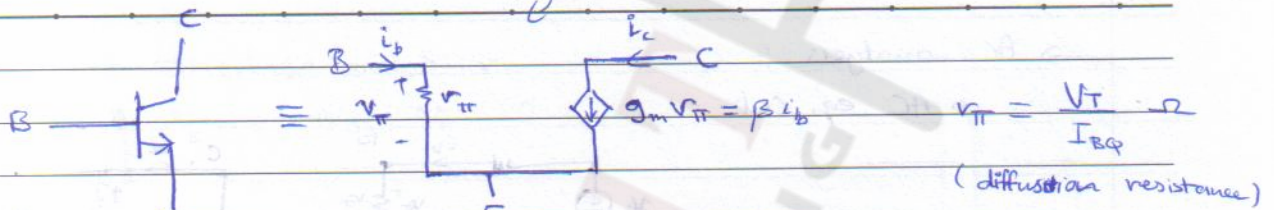
hybrid- π equivalent circuit.

different
units of
parameter.



No. _____

Linear ckt



$$r_{\pi} = \frac{V_T}{I_{BQ}} \quad \Omega$$

(diffusion resistance)

$$g_m = \frac{I_{CQ}}{V_T} \quad (\text{transconductance}), \quad \text{who } (-V)(S) \rightarrow \text{Siemens.}$$

$$r_{\pi} g_m = \frac{I_{CQ}}{I_{BQ}} = \beta$$

$$\Rightarrow \boxed{\beta = r_{\pi} g_m}$$

$$\Rightarrow g_m v_{\pi} = \frac{\beta}{r_{\pi}} \cdot i_b r_{\pi} = \beta i_b$$

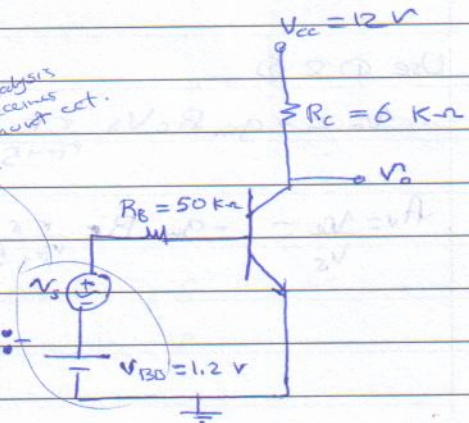
Example 1

$$\beta = 100$$

$$V_{BE(on)} = 0.7 \text{ V}$$

Find the voltage gain ($A_v = \frac{V_o}{V_s}$)

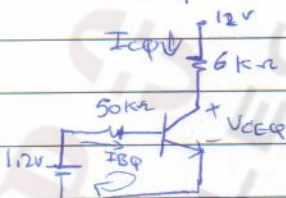
if AC analysis becomes a circuit ckt.



it's not practical :- because there is no capacitor

DC analysis

DC eq. ckt.



input loop

$$-1.2 + 50 I_{BQ} + 0.7 = 0$$

$$I_{BQ} = 10 \mu\text{A}$$

$$\Rightarrow I_{CQ} = \beta I_{BQ} = 1 \text{ mA}$$

output loop

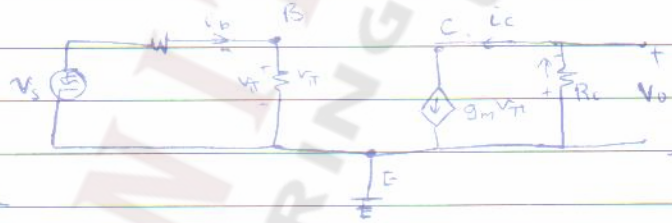
$$-12 + 6 I_{CQ} + V_{CEQ} = 0$$

$$\boxed{V_{CEQ} = 6 \text{ V}} \quad \text{So is Forward}$$

No. _____

→ AC analysis :

→ AC eq. ckt :



$$r_{\pi} = \frac{V_T}{I_{BQ}} = 2.6 \text{ k}\Omega$$

$$g_m = \frac{I_{CQ}}{V_T} = 88.5 \text{ mA/V}$$

$$v_o = -g_m r_{\pi} R_C \quad \text{①}$$

$$v_{\pi} = v_s \frac{r_{\pi}}{r_{\pi} + 50} \quad \text{②}$$

Use ① & ② :

$$v_o = -g_m R_C v_s \frac{r_{\pi}}{r_{\pi} + 50}$$

180° phase-shift between v_s & v_o

$$A_v = \frac{v_o}{v_s} = -g_m R_C \frac{r_{\pi}}{r_{\pi} + 50} \approx -11.4$$

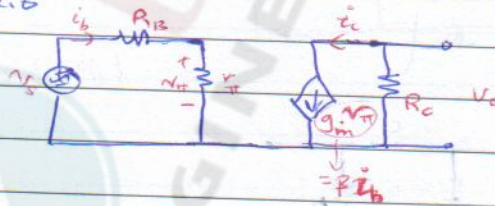
No. _____

② if $v_s(t) = 0.25 \sin \omega t$ V
 Find i_B , i_C , V_{CE} , V_o ?

$$\Rightarrow i_B = I_{BQ} + i_b$$

\downarrow \downarrow
 10 mA v_s
 $R_B + r_{\pi}$

$$\therefore i_B = 10 + 0.25 \sin \omega t \frac{V}{50 + 2.6} = 10 + 4.75 \sin \omega t \text{ mA}$$



$$i_C = \beta i_B$$

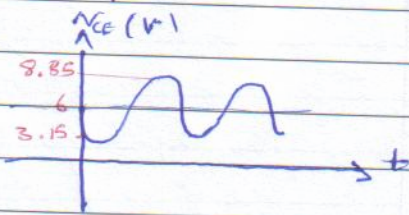
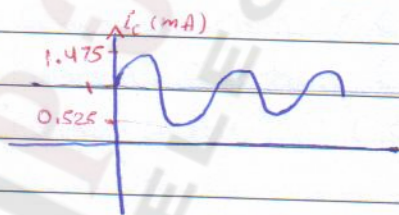
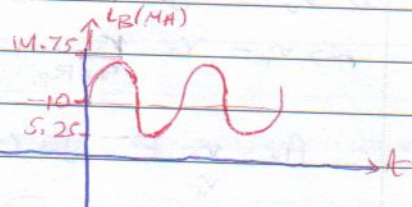
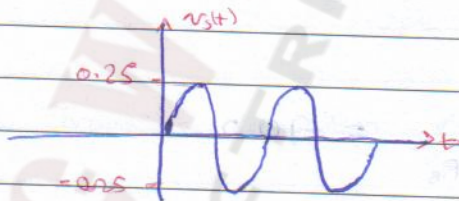
$$= 1 + 0.475 \sin \omega t \text{ mA}$$

$$V_{CE} = V_{CEQ} + v_{ce} = 6 + (-i_C R_C)$$

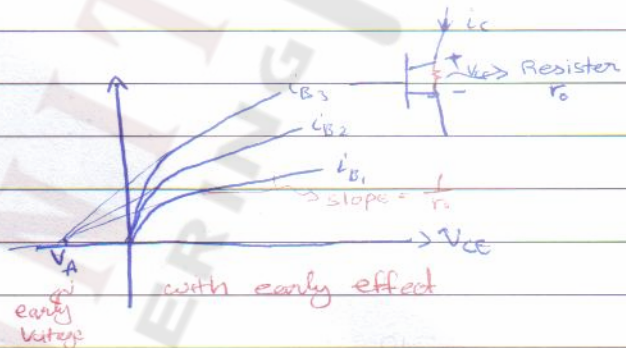
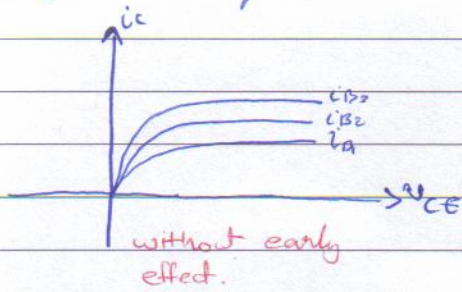
$$= 6 - 0.475 \sin \omega t \times 6$$

$$= 6 - 2.85 \sin \omega t \text{ V}$$

$$\Rightarrow V_o = v_{ce} = 6 - 2.85 \sin \omega t \text{ V}$$

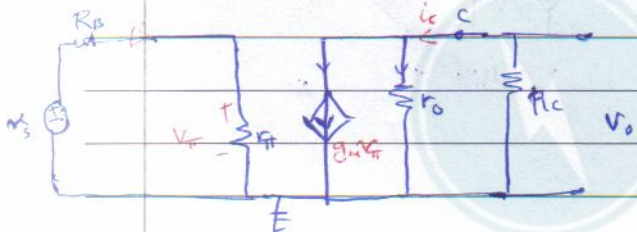


* Hybrid- π equivalent circuit with the early effect.



Very large value

$$r_o = \frac{V_A}{I_{CQ}} \approx \infty$$



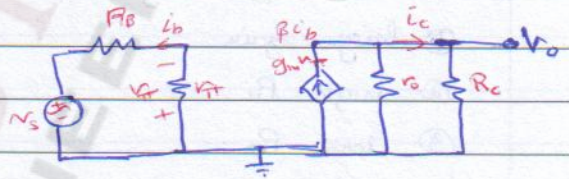
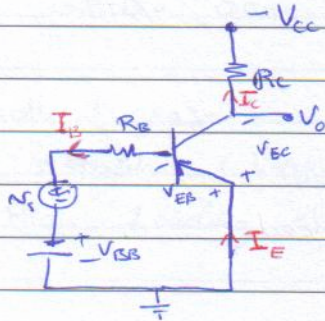
Ex: For the last example, if $V_A = 50$ V
Find A_v .

$$v_o = -g_m v_{\pi} (r_o \parallel R_C)$$

$$\rightarrow v_{\pi} = v_s \frac{R_{\pi}}{R_{\pi} + R_B}$$

$$\therefore A_v = \frac{v_o}{v_s} = -g_m (r_o \parallel R_C) \frac{R_{\pi}}{R_{\pi} + R_B} = -10.2$$

PNP BJT :-



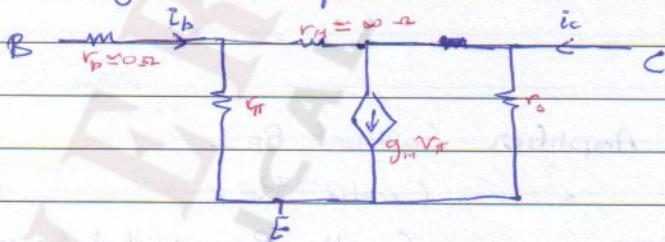
⇒ AC circuit :-

$$\Rightarrow V_o = g_m v_{\pi} (r_o \parallel R_C)$$

$$v_{\pi} = \frac{-v_s R_{\pi}}{R_{\pi} + R_B}$$

$$\hookrightarrow A_v = -g_m (r_o \parallel R_C) \frac{R_{\pi}}{R_{\pi} + R_B}$$

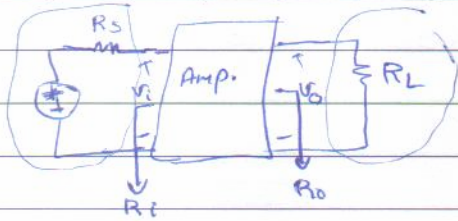
⊗ Expanded Hybrid-π equivalent circuit :-



⊗ Basic Transistor amplifier (practical amplifiers) configurations :-

- ① Common emitter (CE) Amplifier
- ② Common collector (CC) Amplifier
- ③ Common base (CB) Amplifier

Common emitter amplifier: output is inverted and larger than input.



* For a good Voltage Amplifier, we need:

- ① high gain
- ② high R_i
- ③ low R_o

* For a good current Amplifier, we need:

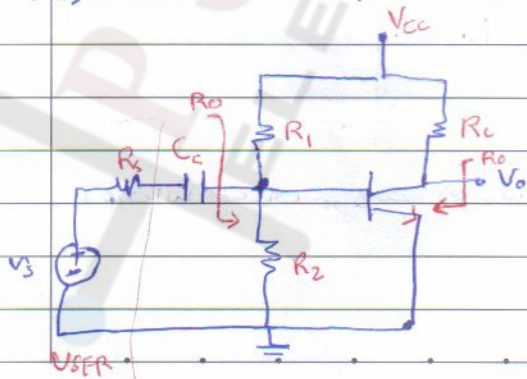
- ① high gain
- ② low R_i
- ③ high R_o

④ CE Amplifier:-

Types:

- ① Basic CE Amplifier (without R_E).
- ② " " " (with R_E)
- ③ " " " (with R_E and bypass capacitor).
- ④ Advanced CE amplifier.

→ Basic CE amplifier (without R_E):-



C_c : coupling capacitor to block any DC value from the user (So, the user cannot change the position of Q-point).

⇒ Advantages :-

High voltage gain.

⇒ Disadvantages :-

① Unstable (Very sensitive to V_{BE} (on)).

② High Loading effect. (R_i is not very high).

Example + IF $V_{CC} = 12\text{ V}$, $R_C = 6\text{ K}\Omega$, $R_1 = 93.7\text{ K}\Omega$, $R_2 = 6.3\text{ K}\Omega$

$\beta = 100$, $V_{BE} = 0.7\text{ V}$, $V_A = 100\text{ V}$

Find the voltage gain, R_i , R_o } \rightarrow calculate r_o

* DC analysis +

$$R_{Th} = R_1 \parallel R_2 =$$

$$V_{Th} = 12 \cdot \frac{R_2}{R_1 + R_2}$$

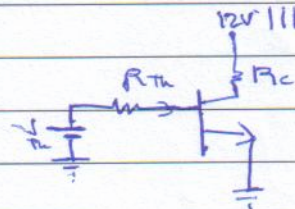
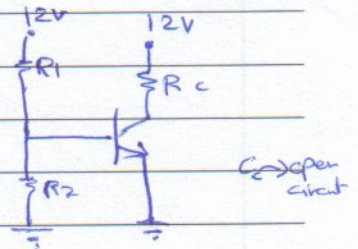
$$\rightarrow -V_{Th} + I_{BQ} R_{Th} + 0.7 = 0$$

$$I_{BQ} = 9.5\text{ }\mu\text{A}$$

$$I_{CQ} = 0.95\text{ mA}$$

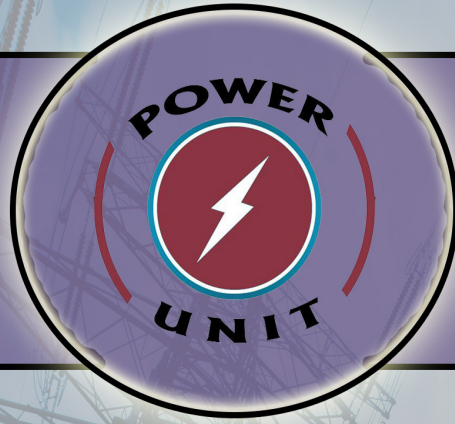
$$\rightarrow V_{CEQ} = 6.31\text{ V} > V_{CE(sat)}$$

✓ (Forward)



* AC analysis :-

⇒ short circuit

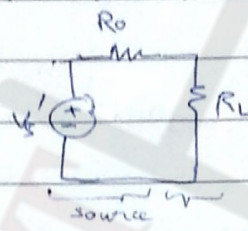
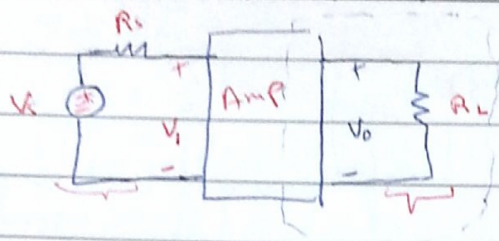


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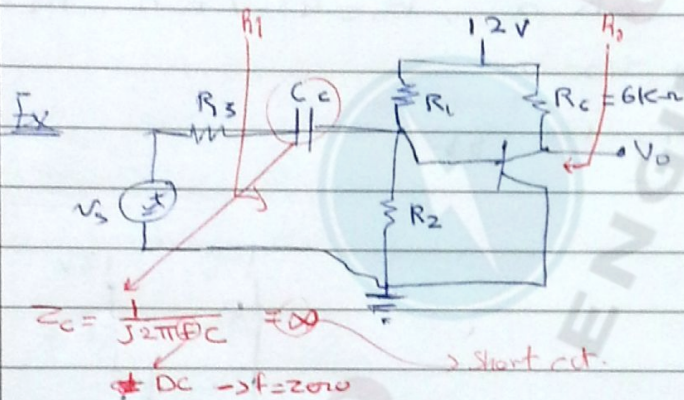
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3 & 4 week



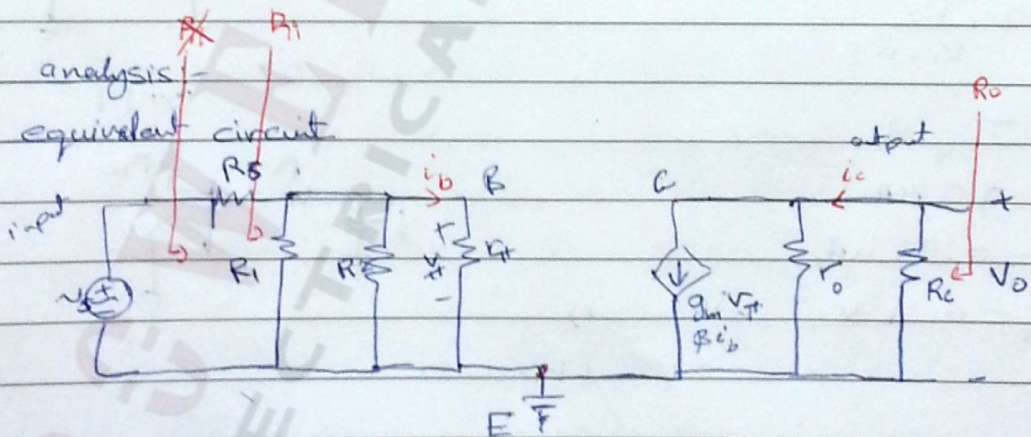
$V_i \approx V_s \rightarrow$ (small loading effect, good)
 $V_i \ll V_s \rightarrow$ (high loading effect, bad).

$V_o \approx V_s \rightarrow$ (small loading effect)
 $V_o \ll V_s \rightarrow$ (high loading effect).



$$Z_c = \frac{1}{j\omega C_c} = \infty$$

* AC analysis -
 AC equivalent circuit



$$r_{\pi} = \frac{V_T}{I_{BQ}} = 2.74 \text{ K}\Omega$$

$$g_m = \frac{I_{CQ}}{V_T} = 36.5 \text{ mA/V}$$

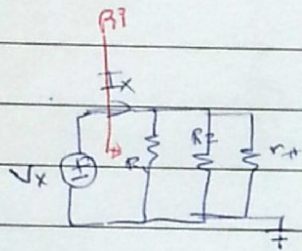
$$r_o = \frac{V_A}{I_{CQ}} = 105 \text{ K}\Omega$$

$$A_v = \frac{V_o}{V_s}$$

$$V_o = -g_m V_{\pi} (r_o \parallel R_c) \quad (1)$$

$$V_{\pi} = \frac{V_s (r_{\pi} \parallel R_1 \parallel R_2)}{(r_{\pi} \parallel R_1 \parallel R_2) + R_s} \quad (2)$$

$$A_v = -g_m (r_o \parallel R_c) \frac{(r_{\pi} \parallel R_1 \parallel R_2)}{(r_{\pi} \parallel R_1 \parallel R_2) + R_s} = -163$$



and kill all independent sources.

$$R_i = \frac{V_x}{I_x}$$

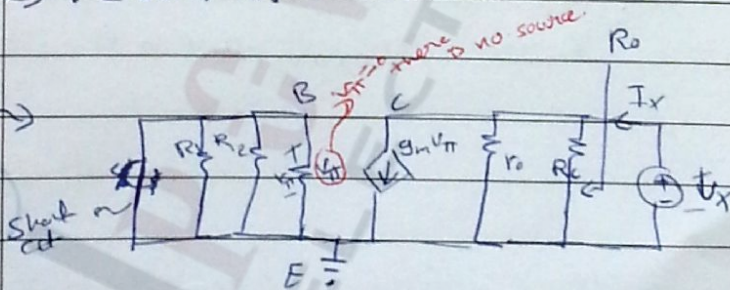
$$-V_x + I_x (R_1 \parallel R_2 \parallel r_{\pi}) = 0$$

$$\rightarrow R_i = \frac{V_x}{I_x} = R_1 \parallel R_2 \parallel r_{\pi} = 1.87 \text{ k}\Omega$$

$R_i \gg R_s \rightarrow$ so high loading effect

$$V_i = V_s \times \frac{R_i}{R_i + R_s} = 0.789 V_s$$

$\rightarrow V_i \approx 80\% V_s$



high load \rightarrow high R_o
low \rightarrow low R_o

$V_s =$ short ckt $\rightarrow V_{\pi} = \text{zero}$

$\rightarrow g_m V_{\pi} = \text{zero}$ (open ckt).

$$R_o = \frac{V_x}{I_x} = r_o \parallel R_c \quad \text{so } \rightarrow R_o = 5.68 \text{ k}\Omega$$

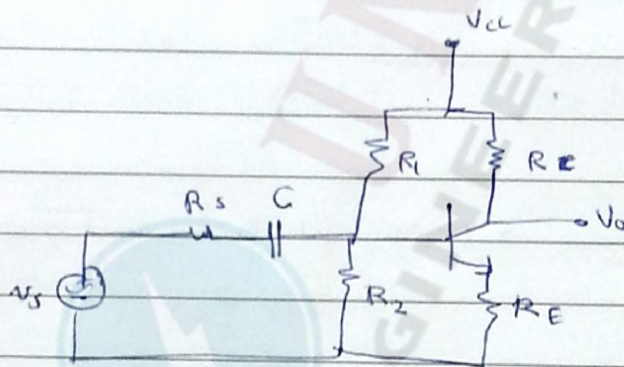


its sensitive for $V_{BE(on)}$:-

→ For $V_{BE(on)} = 0.7 \text{ V}$ → $V_{CEQ} = 6.51 \text{ V}$ (Forward active Mo)

→ For $V_{BE(on)} = 0.6 \text{ V}$ → $V_{CEQ} = -3.6 \text{ V}$ (not in Forward ad)

⊗ CE Amplifier with R_E :-



Advantages :-

- ① Stable Amplifier (A_v is less dependent on β).
- ② Small loading effect (R_i is high).

Disadvantage :-

Small A_v

EX :-

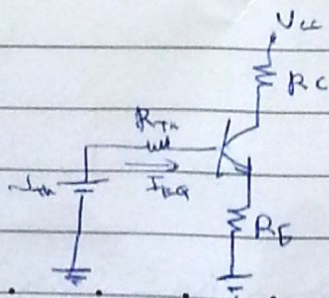
$V_{CC} = 10 \text{ V}$, $R_C = 2 \text{ k}\Omega$, $R_1 = 56 \text{ k}\Omega$, $R_2 = 12.2 \text{ k}\Omega$

$R_E = 0.4 \text{ k}\Omega$, $R_S = 0.5 \text{ k}\Omega$, $\beta = 100$, $V_{BE(on)} = 0.7 \text{ V}$

($V_A = \infty$) → $r_o = \infty$ (open cd)

Find A_v and R_i ?

DC analysis :-



$$\Rightarrow R_{TH} = R_1 // R_2 = 10 \text{ k}\Omega$$

$$\Rightarrow V_{TH} = V_{CC} \frac{R_2}{R_2 + R_1} = 1.785 \text{ V}$$

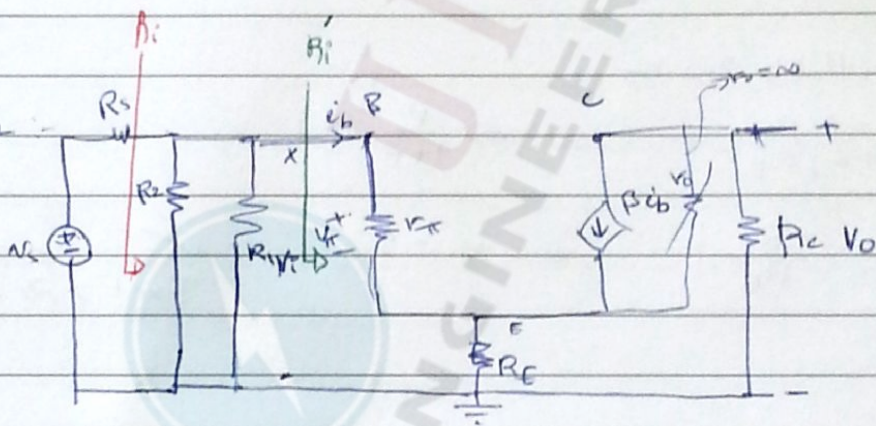
$$\rightarrow -V_{th} + R_{th} I_{BQ} + 0.7 + R_E I_{EQ} = 0$$

$$I_{EQ} = 21.6 \text{ mA}$$

$$I_{CQ} = \beta I_{BQ} = 2.16 \text{ mA}$$

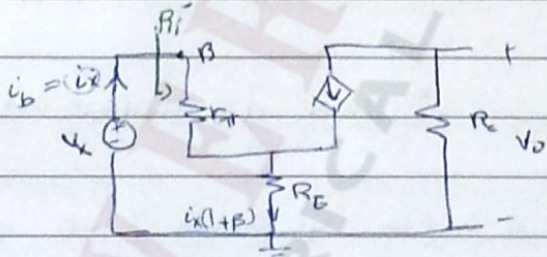
$$\rightarrow V_{CEQ} = 4.81 \text{ V} > V_{CE(sat)} \quad \checkmark \text{ Forward.}$$

AC analysis



$$R_i = R_1 // R_2 // R_i'$$

to find R_i' :-



$$-V_x + i_x r_{\pi} + (1 + \beta) i_x R_E = 0$$

$$R_i' = \frac{V_x}{I_x} = r_{\pi} + (1 + \beta) R_E = 41.6 \text{ k}\Omega$$

$$R_i = R_1 // R_2 // R_i' = 8.06 \text{ k}\Omega \gg R_s \text{ (small loading effect).}$$

$$\rightarrow A_v = \frac{V_o}{V_i}$$

$$V_o = -\beta i_b R_c \quad \text{--- (1)}$$

$$V_i = V_s * \frac{(R_1 // R_2 // R_i')}{R_1 // R_2 // R_i' + R_s}$$

$$\rightarrow i_b = \frac{V_i}{R_i'}$$

$$A_v = \frac{V_o}{V_i} = \frac{-\beta R_c}{r_{\pi} + (1+\beta)R_E} \left(\frac{R_i}{R_i + R_s} \right)$$

$$\approx -4.53 \quad (\text{small gain}).$$

\Rightarrow Since $R_i \gg R_s$

$$A_v \approx \frac{-\beta R_c}{r_{\pi} + (1+\beta)R_E} \quad (1)$$

also, $(1+\beta)R_E \gg r_{\pi}$

$$\therefore A_v \approx \frac{-\beta R_c}{(1+\beta)R_E} \rightarrow \frac{\beta}{1+\beta} \approx 1$$

$$\therefore A_v \approx \frac{-R_c}{R_E}$$

$$\approx -5$$

✓
Exact value is -5

β	A_v
50	-4.41
100	-4.53
150	-4.57

\hookrightarrow is less dependant on β .

For stability: (to get a stable Q-points), we need

$$(1+\beta)R_E \gg R_{Th}$$

$$(1+\beta)R_E \gg R_{Th}$$

$$\rightarrow R_{Th} = 0.1(1+\beta)R_E$$

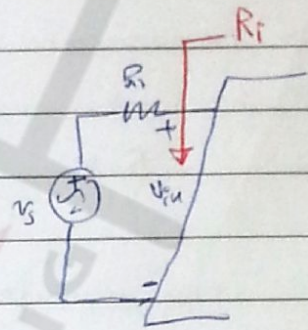
$$\downarrow$$

$$R_1 \parallel R_2$$

For the last examples:
loading effect:

2.06

$$V_{in} = ? \quad V_s \frac{R_i}{R_i + R_s} = 0.912 V_s$$



$$V_{in} = 0.912 V_s \quad (\text{small loading effect})$$

④ Common E, CE amplifier with R_E and bypass capacitor:

C_c : Coupling Capacitor

C_E : Bypass Capacitor. Why?

for CE with $R_E \Rightarrow$

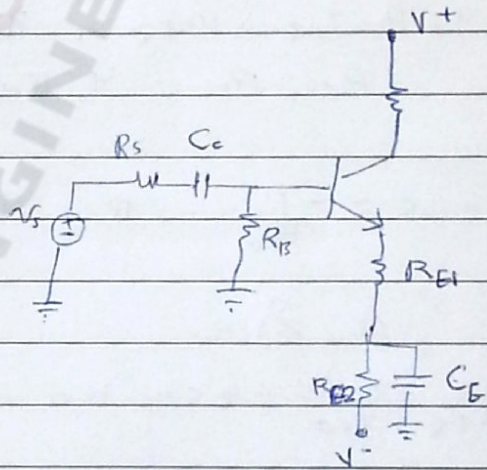
we need $(1+\beta)R_E \gg R_{th}$

(For stable Q point),

so, we need high R_E

\Rightarrow but we also need high gain $A_v = -\frac{R_c}{R_E} \Rightarrow$ so, we need small R_E .

So, we use the bypass capacitor to satisfy both AC and DC requirement.



EX: Consider CE amplifier with R_E . Use the approximate

gain $A_v = -\frac{R_c}{R_E}$, given that $I_{CQ} = 1 \text{ mA}$, $V_{CEQ} = 5 \text{ V}$,

$\beta = 99$, $V_{CC} = 9 \text{ V}$.

and $A_v = -8$, $R_i = 27.5 \text{ k}\Omega$

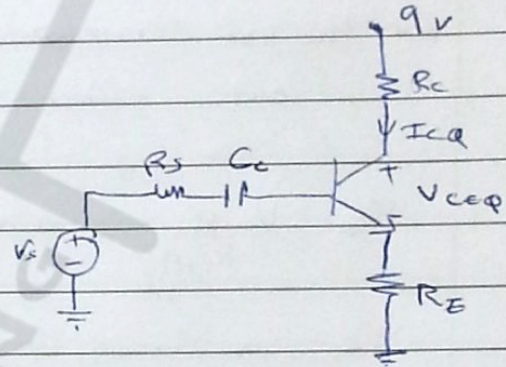
$R_1 // R_2 \approx \infty$ (open ckt)

$I_{CQ} = I_{EQ}$

Find R_E and R_C

⇒ DC requirements :-

- ① $I_{CQ} = 1 \text{ mA}$
- ② $V_{CEQ} = 5 \text{ V}$



⇒ AC requirements :-

- ① $A_v = -8$
- ② $R_i = 27.5 \text{ k}\Omega$

▷ output loop:

$$-9 + R_C I_{CQ} + V_{CEQ} + R_E I_{EQ} = 0$$

$$R_C + R_E = 4 \text{ k}\Omega \quad (1)$$

$$A_v = -8 = -\frac{R_C}{R_E} \Rightarrow R_C = 8 R_E$$

$$R_i = R_1 \parallel R_2 + (1 + \beta) R_E$$

$$27.5 \text{ k} = \frac{V_T}{I_{BQ}} = \frac{V_T (\beta + 1)}{I_{CQ}} \approx 2.574 \text{ k}\Omega \Rightarrow R_E = 0.25 \text{ k}\Omega$$

$$R_C = 8(R_E) = 2 \text{ k}\Omega$$

$R_C + R_E = 4 \text{ k}\Omega$ → problem → sol: use bypass capacitor.
 conflict

⇒ Bypass capacitor (on R_E)

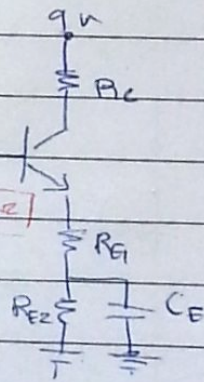
▷ DC requirement: (C_E open ckt)

$$R_C + R_{E1} + R_{E2} = 4 \quad (1) \Rightarrow R_{E2} = 1.75 \text{ k}\Omega$$

⇒ AC requirement: (C_E short ckt)

$$R_C = 8 R_{E1} \quad (2) \Rightarrow R_C = 2 \text{ k}\Omega$$

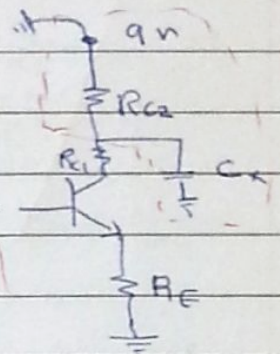
$$R_i = R_1 \parallel R_2 + (1 + \beta) R_{E1} \Rightarrow R_{E1} = 0.25 \text{ k}\Omega$$



Bypass Capacitor on R_E :-

⇒ DC requirement :-

$$R_B + R_{C2} + R_E = 4 \quad (1)$$



$R_{C2} = 1.75 \text{ k}\Omega$

⇒ AC requirement :-

$$R_B = 8 R_E$$

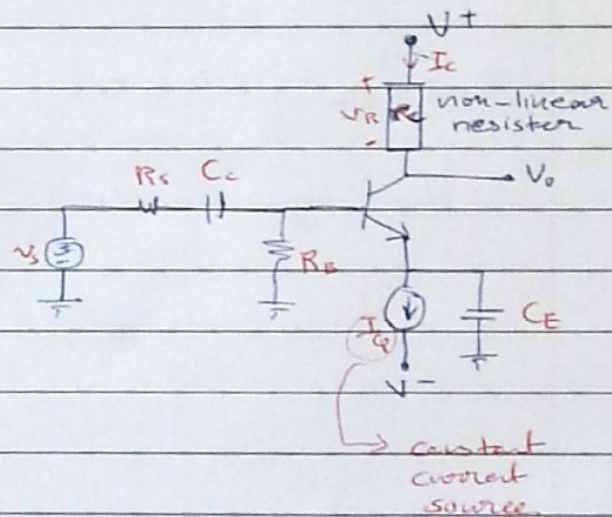
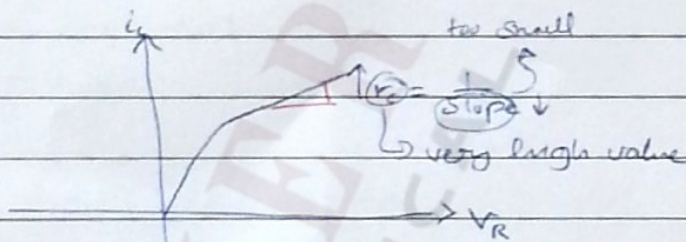
$R_B = 2 \text{ k}\Omega$

$$\Rightarrow R_E = R_B / 8 = 2 \text{ k}\Omega / 8 = 0.25 \text{ k}\Omega = 250 \Omega$$

(*) Advanced CE amplifier :-

Advantages :-

Very high A_v (voltage gain).



Ex :- if $I_Q = 0.5 \text{ mA}$, $\beta = 120$, $V_A = 80 \text{ V}$, $V_C = 120 \text{ k}\Omega$, $R_B = 0 \Omega$, Find $A_v = \frac{V_O}{V_i}$?

DC analysis :-

$$\Rightarrow I_{EQ} = I_Q = 0.5 \text{ mA} \quad (C_C \text{ open ckt})$$

$$I_{CQ} = \frac{\beta}{1 + \beta} I_{EQ}$$

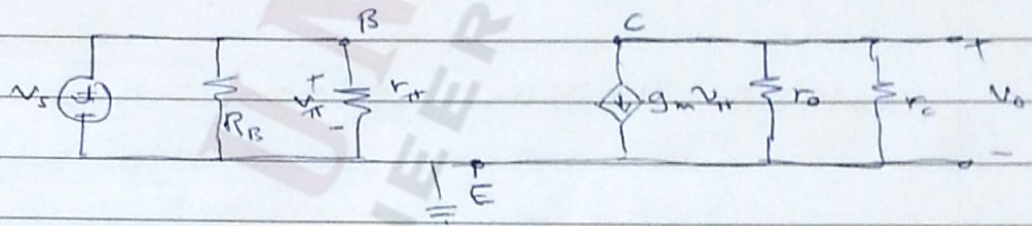
$$I_{CQ} \approx I_{EQ} = 0.5 \text{ mA}$$

AC analysis:

$$r_{\pi} = \frac{\beta V_T}{I_{CQ}} =$$

$$g_m = \frac{I_{CQ}}{V_T} = 19.2 \text{ mA/V}$$

$$r_o = \frac{V_A}{I_{CQ}} = 160 \text{ k}\Omega$$



$$A_v = \frac{v_o}{v_s} \Rightarrow$$

$$v_o = -g_m \underbrace{v_{\pi}}_{v_s} (r_o \parallel r_c)$$

$$\therefore A_v = -g_m (r_o \parallel r_c) = -1317 \text{ (very high gain)}$$

\hookrightarrow (Kuzo r_c very high)

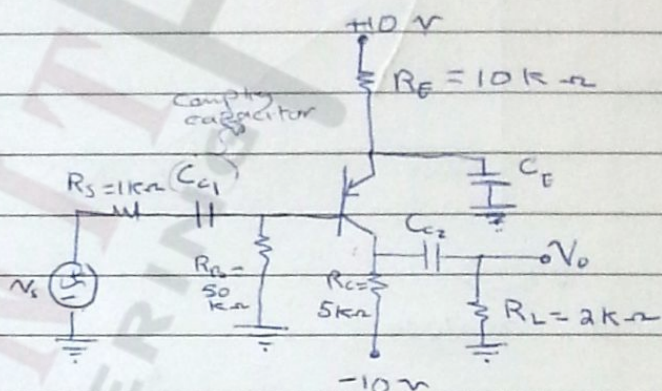
AC load line: $(i_c \propto v_{ce})$

Ex: Given $V_{BE(ON)} = 0.7 \text{ V}$

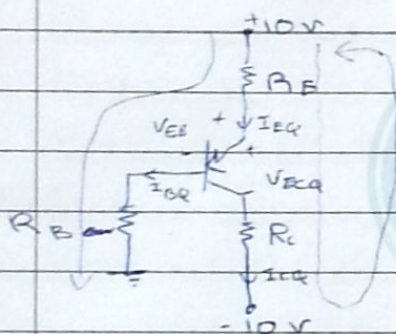
$\beta = 150$

$V_A = \infty \rightarrow r_c = \infty$

⇒ Draw DC & AC load lines.



⇒ DC analysis:



input loop: $-10 + R_E I_{EQ} + 0.7 + R_B I_{BQ} = 0$
 $(1 + \beta) I_{BQ}$

⇒ $I_{BQ} = 5.96 \text{ mA}$

⇒ $I_{CQ} = \beta I_{BQ} = 0.894 \text{ mA}$

output loop: $-10 + R_E I_{CQ} + V_{CEQ} + R_C I_{CQ} + -10 = 0$
 $V_{CEQ} = 6.53 \text{ V}$

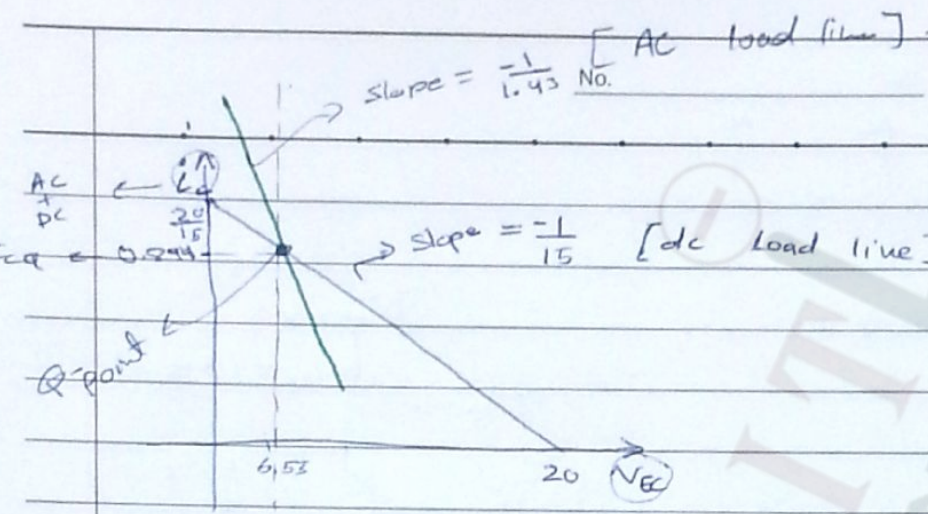
⇒ DC load line: $(I_c \propto V_{ce})$

from output loop: $-10 + R_E \frac{I_c}{\beta} + V_{ce} + R_C I_c - 10 = 0$

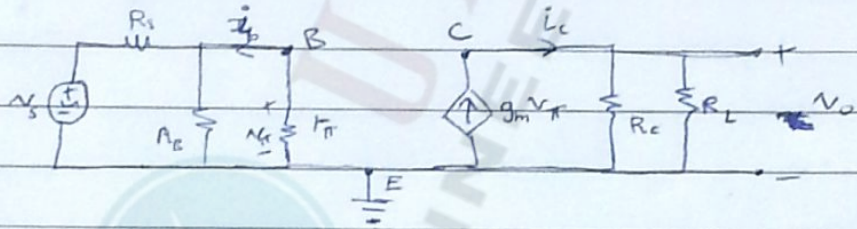
$I_c [R_E (\frac{1+\beta}{\beta}) + R_C] = 20 - V_{ce}$

$I_c = \frac{20 - V_{ce}}{R_E (\frac{1+\beta}{\beta}) + R_C}$

I_c
 I_c
 V_{ce}



AC analysis :-



$$r_{\pi} = \frac{V_T}{I_{BQ}} = 4.36 \text{ k}\Omega$$

$$g_m = \frac{I_{CQ}}{V_T} = 34.4 \text{ mA/V}$$

AC load line = (i_c & V_{EC})

$$i_c = -\frac{V_{EC}}{R_L \parallel R_C}$$

$$\text{Slope} = -\frac{1}{R_L \parallel R_C}$$

⇒ AC load line (slope) → \rightarrow amplification \rightarrow \rightarrow \rightarrow

Note :-

The best value for $V_{CEQ} = \frac{V^+ - V^-}{2}$,

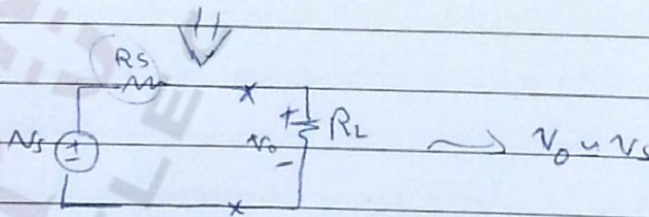
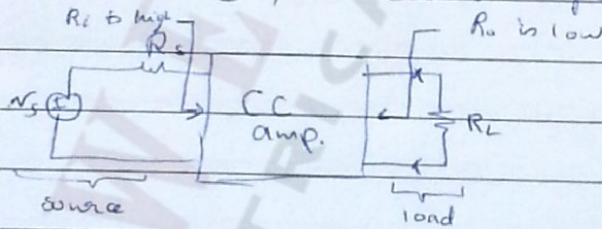
to get the Q point in the mid of forward active region.

⊗ Common Collector Amplifier :- (CC amplifier)

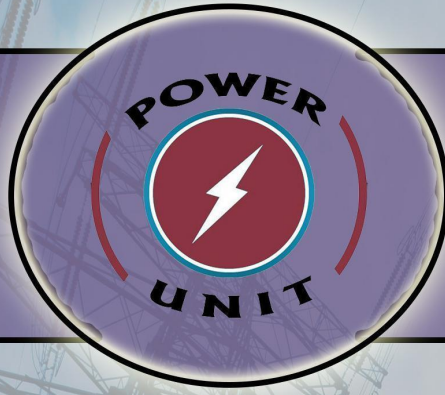
Features:-

- ① High R_i
- ② Low R_o
- ③ $V_o \approx V_i$ ($A_v = 1$)
- ④ Used as the output stage of multistage amplifier.
- ⑤ R_1 and R_2 should be very large to take the advantage of high R_{ib} . $\rightarrow R_i = R_1 \parallel R_2 \parallel R_{ib}$

Due to ① & ②, it is called impedance transformer. OR (buffer)



↓ OR (emitter follower) [the voltage at the emitter follows the input voltage in phase and magnitude].



Amplifiers

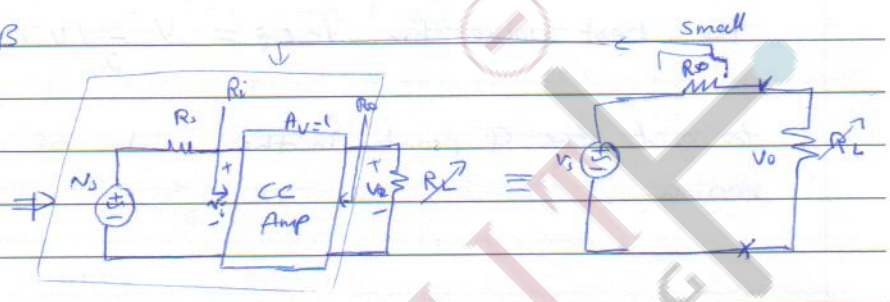
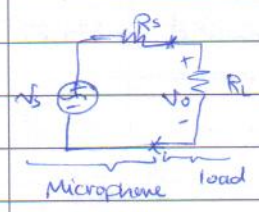
NoteBook

Dr. Ra'ed Al Zo'ubi
By: Lara Abu Sofa

بأفكارنا نبدع

~~Microphone~~

② $A_i = \frac{I_o}{I_i} = 1 + \beta$



R_i very high $V_i = V_o$ small $R_o \Rightarrow V_o \approx V_s$

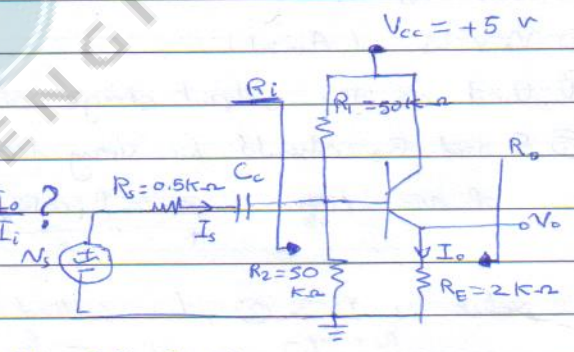
$V_o = V_s \frac{R_L}{R_L + R_s}$

Ex:-

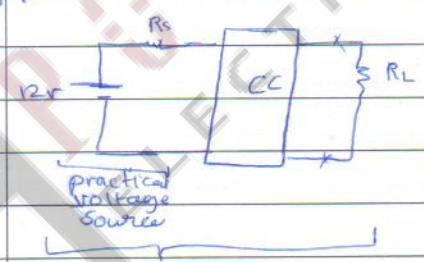
$\beta = 100$

$V_A = 80 \text{ v}$

find $A_v = \frac{V_o}{V_s}$, R_i , R_o , $A_i = \frac{I_o}{I_i}$?



Note \Rightarrow Practical to Ideal source (w/ CC Amp).



\rightarrow Ideal Voltage Source

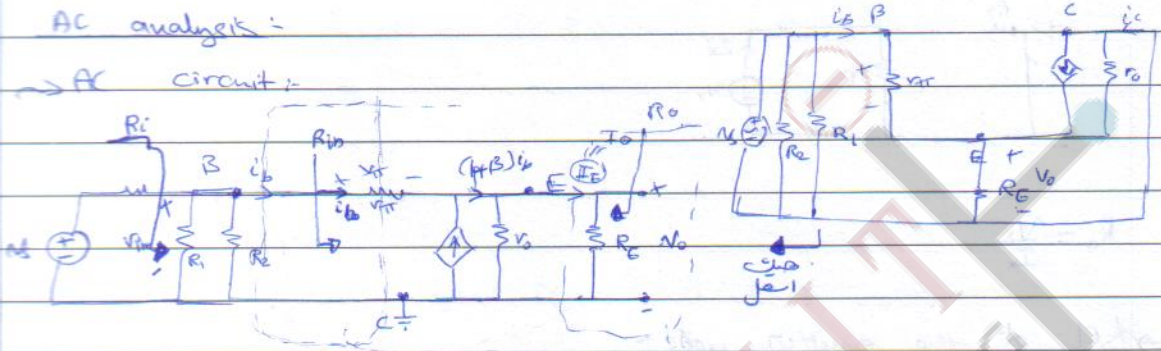
\rightarrow DC analysis:-

$I_{CQ} = 0.793 \text{ mA}$

$V_{EQ} = 3.4 \text{ v}$

AC analysis:

→ AC circuit:



$$r_{\pi} = \frac{\beta V_T}{I_{CQ}} = 3.28 \text{ k}\Omega$$

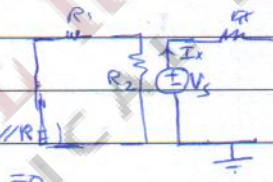
$$g_m = \frac{I_{CQ}}{V_T} = 30.5 \text{ mA/V}$$

$$r_o = \frac{V_A}{I_{CQ}} = 100 \text{ k}\Omega$$

$$\rightarrow R_i = R_1 \parallel R_2 \parallel R_{iB}$$

$$\rightarrow R_{iB} = \frac{V_x}{I_x}$$

$$= V_x + r_{\pi} I_x + (1 + \beta) I_x (r_o \parallel R_E)$$



$$R_{iB} = \frac{V_x}{I_x} = r_{\pi} + (1 + \beta) (r_o \parallel R_E) = 201 \text{ k}\Omega$$

$$R_i = 22.2 \text{ k}\Omega$$

→ (calculating the input resistance of the BJT circuit)

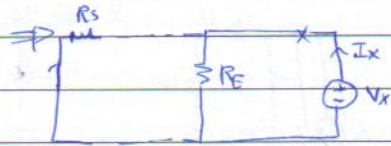
$$\rightarrow A_v = \frac{V_o}{V_s}$$

$$V_{in} = V_s + \frac{R_i}{R_i + R_s}$$

$$i_b = \frac{V_{in}}{R_{iB}}$$

$$V_o = (1 + \beta) i_b (r_o \parallel R_E)$$

$$\rightarrow A_v = \frac{(1 + \beta) (r_o \parallel R_E)}{r_{\pi} + (1 + \beta) (r_o \parallel R_E)} \cdot \left(\frac{R_L}{R_i + R_s} \right) = 0.962 \text{ V/V}$$



$$R_o = \frac{V_x}{I_x}$$

→ KCL at the emitter node

$$\sum i_{in} = \sum i_{out}$$

$$I_x + g_m v_{\pi} + \frac{V_x}{R_E} = \frac{V_x}{R_E} + \frac{V_x}{r_o}$$

$$v_{\pi} = -V_x \cdot \frac{R_E}{R_E + R_S \parallel R_1 \parallel R_2}$$

$$\Rightarrow R_o = \frac{V_x}{I_x} = \left(r_{\pi} + \frac{R_1 \parallel R_2 \parallel R_S}{1 + \beta} \right) \parallel R_E \parallel r_o = 36.6 \Omega$$

Small

$$\Rightarrow A_i = \frac{I_o}{I_s}$$

$$I_o = (1 + \beta) I_b \frac{r_o}{r_o + R_E}$$

$$I_b = I_s \frac{R_1 \parallel R_2}{R_{ib} + R_1 \parallel R_2}$$

$$A_i = (1 + \beta) \left(\frac{R_1 \parallel R_2}{R_1 \parallel R_2 + R_{ib}} \right) \left(\frac{r_o}{r_o + R_E} \right)$$

~~Small signal~~

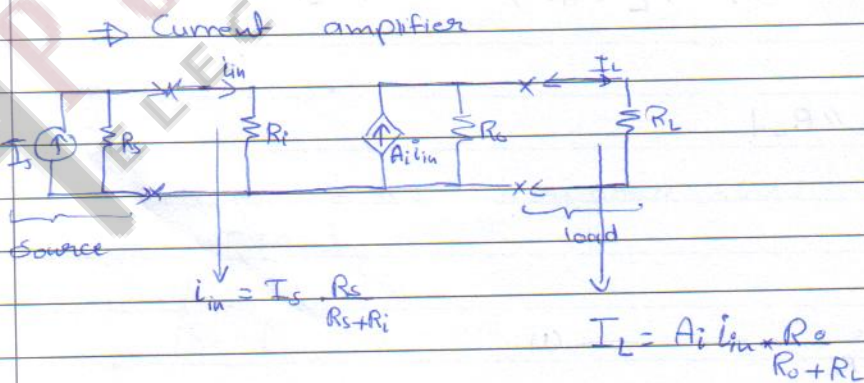
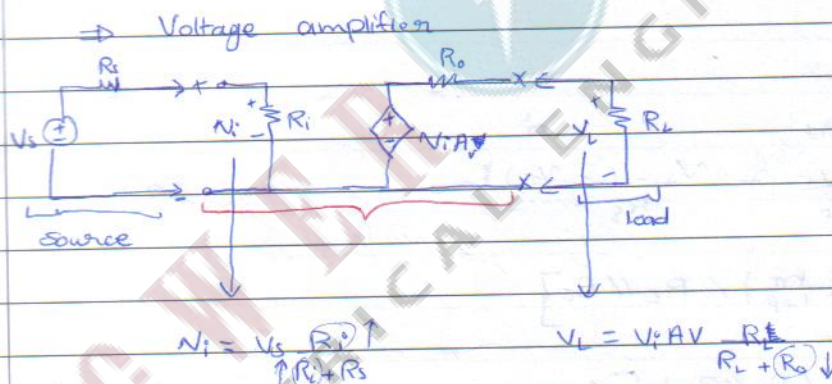
$$A_i \approx (1 + \beta) \text{ if } R_1 \parallel R_2 \gg R_{ib}$$

Common Base Amplifier (CB) :-

Feature :-

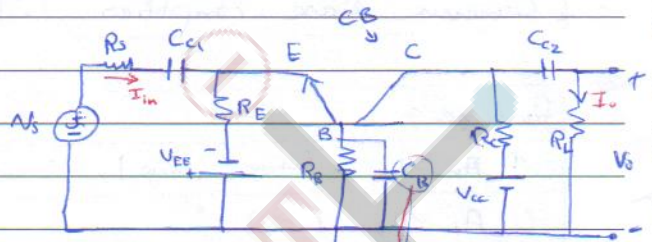
- ① $A_v > 1$ (+ve value)
- ② $A_i \leq 1$ (α)
- ③ Used if the input signal is a current
- ④ Small R_i \uparrow
- ⑤ \rightarrow high R_o \downarrow
- ⑥ It looks almost like Ideal current source.

Note:- Any amplifier circuit can be represented by a two-part network.

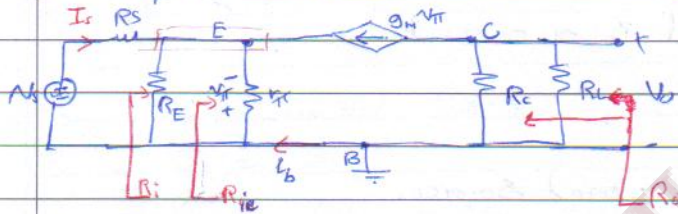


Example :-

Find R_i , R_o , A_i , A_v ?



→ AC equivalent circuit :-



⊕ $A_v = \frac{V_o}{V_s}$

→ $V_o = -g_m v_{\pi} (R_C || R_L)$ (1)

Kcl at node E:

$\sum i_{in} = \sum i_{out}$

$g_m v_{\pi} + \frac{v_E}{r_{\pi}} + \frac{v_E}{R_E} + \frac{V_s}{R_s} - (-v_{\pi}) = 0$ (2)

$v_{\pi} = -\frac{V_s}{R_s} \left[\left(\frac{r_{\pi}}{1+\beta} \right) || R_E || R_s \right]$

→ $A_v = \frac{V_o}{V_s} = +g_m \left(\frac{R_C || R_L}{R_s} \right) \left[\left(\frac{r_{\pi}}{1+\beta} \right) || R_E || R_s \right]$

→ IF $R_s \rightarrow 0$

$A_v \approx +g_m (R_C || R_L)$

⊕ $A_i = \frac{I_o}{I_s}$

$I_o = -g_m v_{\pi} \frac{R_C}{R_C + R_L}$ (1)

Kcl at node E :-

$I_s + g_m v_{\pi} + \frac{v_E}{R_E} + \frac{v_E}{r_{\pi}} = 0$ (2)

No. _____

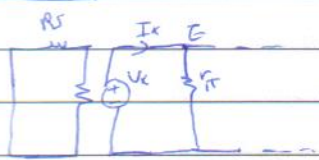
$$V_{\pi} = -I_s \left(g_m + \frac{1}{R_c} + \frac{1}{r_{\pi}} \right)^{-1}$$

$$\Rightarrow A_i = g_m \left(\frac{R_c}{R_c + R_L} \right) \left[\left(\frac{r_{\pi}}{1 + \beta} \right) \parallel R_E \right]$$

$$\Rightarrow \text{IF } R_c \rightarrow \infty$$

$$R_L \rightarrow 0$$

$$\therefore A_i = \frac{g_m r_{\pi}}{1 + \beta} = \frac{\beta}{1 + \beta} = \alpha$$



$$R_i = R_E \parallel R_{ie}$$

$$R_{ie} = \frac{V_x}{I_x}$$

→ KCL at E :-

$$I_x - \frac{V_x}{r_{\pi}} - g_m V_x = 0$$

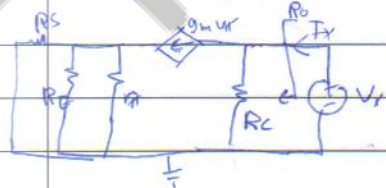
$$I_x = V_x \left(\frac{1}{r_{\pi}} + g_m \right)$$

$$= \frac{V_x (1 + \beta)}{r_{\pi}}$$

$$\Rightarrow R_{ie} = \frac{V_x}{I_x}$$

$$= \frac{r_{\pi}}{1 + \beta}$$

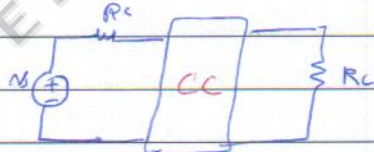
∴ $R_i = R_E \parallel R_{ie} \approx R_{ie}$ (very small value).



$$R_o = \frac{V_x}{I_x}$$

$$\text{KCL at E :- } g_m V_{\pi} + \frac{V_x}{r_{\pi}} + \frac{V_x}{R_E} + \frac{V_x}{R_S} = 0 \rightarrow$$

Note:



No. _____

$$V_{\pi} \left(g_m + \frac{1}{r_{\pi}} + \frac{1}{R_E} + \frac{1}{R_S} \right) = 0$$

$$V_{\pi} = 0 \rightarrow g_m V_{\pi} = 0 \rightarrow R_O = R_{E1}$$



POWER ELECTRONICS ENGINEERING





Amplifiers

NoteBook

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بأفكارنا نبدع

$$V_{T1} \left(g_m + \frac{1}{r_{\pi}} + \frac{1}{R_E} + \frac{1}{R_S} \right) = 0$$

$$V_{T1} = 0 \rightarrow g_m V_{T1} = 0 \rightarrow R_O = R_C$$

Multi-stage amplifier :

في كل stage ن DC analysis

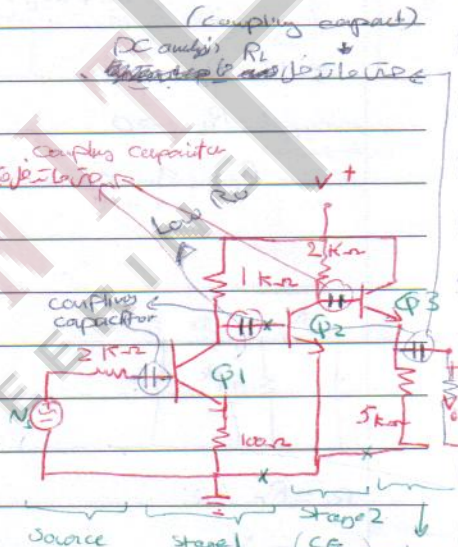
Ex :

Given For $Q_1, Q_2, Q_3, \beta = 100$

for $Q_1, r_{\pi} = 1 \text{ k}\Omega$

for $Q_2, Q_3, r_{\pi} = 0.5 \text{ k}\Omega$

Find $A_v = \frac{V_o}{V_s}$?



In DC analysis $I_B = 0 \rightarrow \infty$ we will add a resistors (if it was practical).

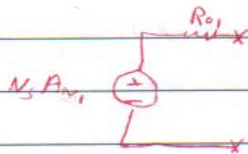
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Source	stage 1 (CE with R_E)	stage 2 (CE without R_E)	stage 3 (CE)
	R_{i1}	R_{i2}	R_{i3}
	R_{o1}	R_{o2}	R_{o3}
	(A_{v1})	(A_{v2})	(A_{v3})

ANS:

Stage 1, CE with R_E



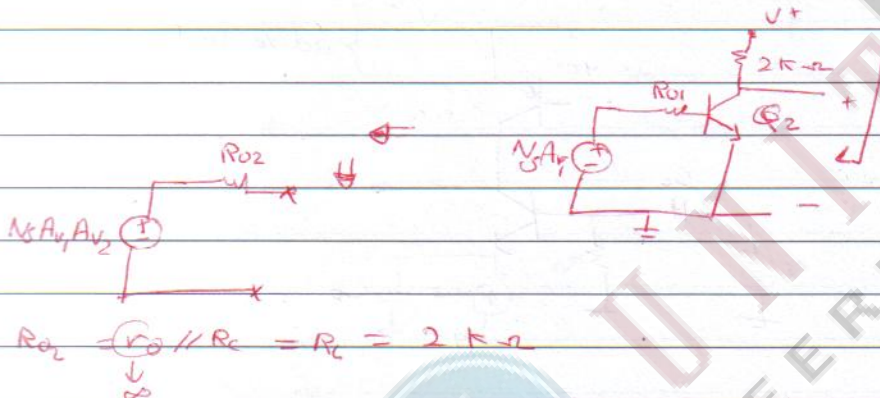
$$\Rightarrow R_O = R_C = 1 \text{ k}\Omega$$

$$\Rightarrow A_{v1} = \frac{-\beta R_C}{r_{\pi} + (1 + \beta) R_E} \left(\frac{R_i}{R_i + R_s} \right)$$

$$R_i = R_1 \parallel R_2 \parallel (r_{\pi} + (1 + \beta) R_E) \approx r_{\pi} + (1 + \beta) R_E$$

$\rightarrow A_{v1} = -7.63$

\Rightarrow Stage 2: (CE without R_E)



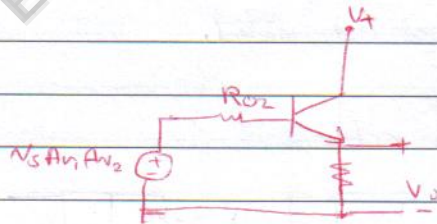
$R_{o2} = R_C \parallel R_L = R_C = 2\text{ k}\Omega$

$A_{v2} = -g_m \left(\frac{R_C \parallel R_L}{R_{B1} \parallel R_2 \parallel r_{\pi} + R_S} \right) (R_C \parallel R_L) = -133$


\Rightarrow Stage 3: (CC)


$A_{v3} = 1$

$N_o = (N_s A_{v1} A_{v2}) A_{v3}$
 $A_{v5} = \frac{N_o}{N_s} = A_{v1} A_{v2} A_{v3}$
 $A_{v5} = +1010$



$\Rightarrow [A_{v5}, R_{o5}] \rightarrow$ \rightarrow Stage 4
 A_{v5} is the overall voltage gain

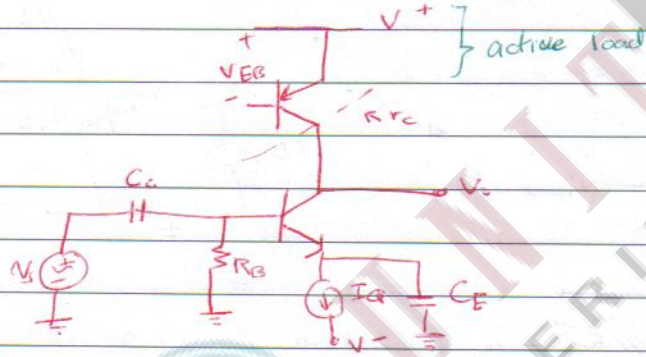
Passive element


Active element


No. _____

* Special Circuits :-

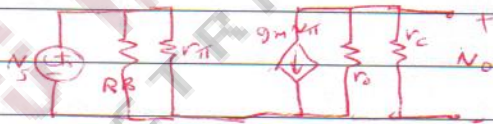
⇒ Advanced CE Amplifier using active load



Why do we use active load?

- ① Small size, so it can be used inside ICs.
- ② r_c is very high $\rightarrow A_v =$ very high value
- ③ Resistors will need bypass capacitor but active load does not need.

AC eq. ckt -



$$\rightarrow V_o = -g_m V_{\pi} (r_o \parallel r_c)$$

$$\rightarrow V_{\pi} = V_i$$

$$\rightarrow A_v = -g_m (r_o \parallel r_c) \rightarrow \text{high } A_v$$

↑ First

analysis

No. _____

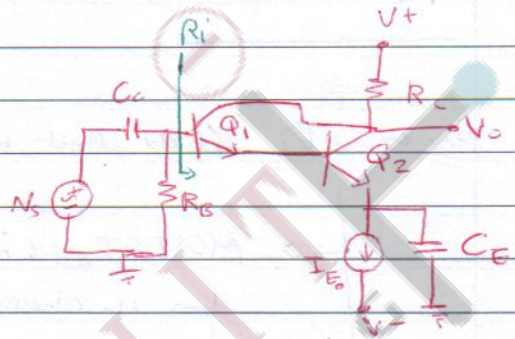
→ Darlington pair circuit :-

→ Features :-

① High Current gain

$$A_i \approx \beta_1 \beta_2$$

② Input resistance is large ($R_i \approx 2\beta_1 r_{\pi 2}$)



→ Cascode Configuration :-

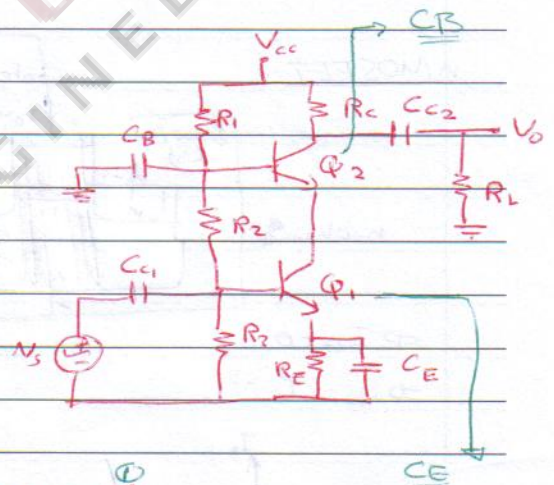
(Cascode ← CB, CE, CE)

→ Features :-

CB has bandwidth wider than CE, but low input impedance of CB is a limitation for many applications.

→ but cascode configuration has wide

bandwidth, moderately high input impedance, high output impedance, high gain as CE.

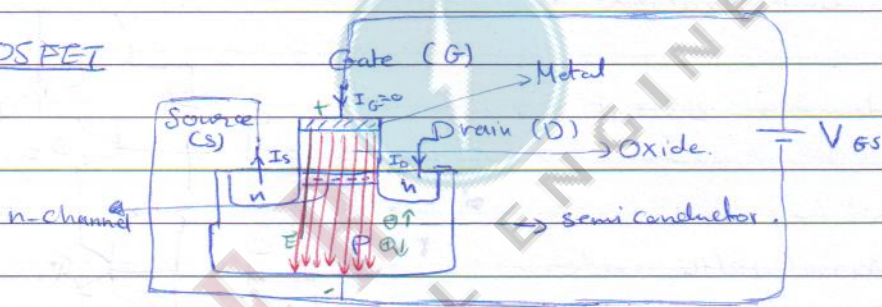


FET Amplifiers:

Review: FET (field effect transistor)

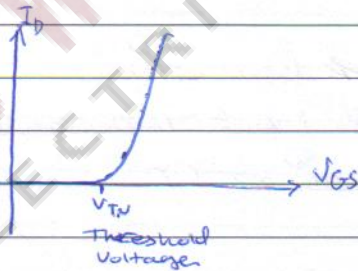
- ① MOSFET (metal-oxide semiconductor FET)
 - ↳ n-channel MOSFET (nMOSFET) (enhancement, depletion)
 - ↳ p-channel MOSFET (PMOSFET) (enhancement, depletion)
- ② JFET (Junction FET)

nMOSFET

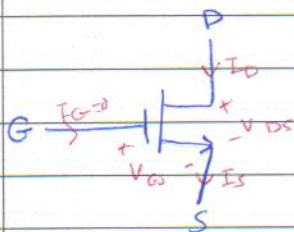


$\Rightarrow I_G = 0$

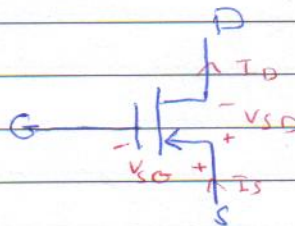
$\Rightarrow I_D = I_S$

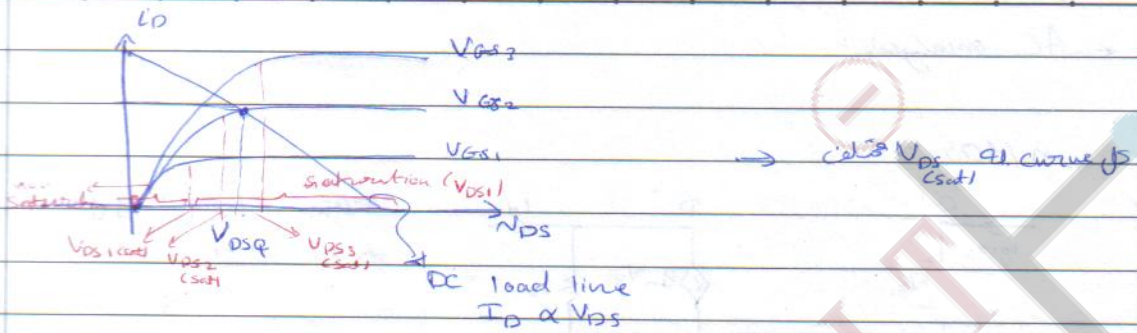


nMOSFET



pMOSFET





⇒ MOSFET Amplifier Configuration

- ① Common Gate
- ② Common Source
- ③ Common Drain

← Advantage of using MOSFET (compared with BJT)

- ① Small size
- ② Low power dissipation
- ③ High Input Impedance

← But, g_m of MOSFET \ll g_m of BJT.

⇒ $A_{v(BJT)} \gg A_{v(FET)}$

← DC analysis

⇒ $I_G = 0$

⇒ $I_D = I_S$

⇒ $I_{DQ} = K_n (V_{GSQ} - V_{TN})^2$

K_n : conduction parameter (mA/V²)

⇒ FET to work as amplifier, it should be in saturation mode. If $V_{DS} > |V_{DS(sat)}|$, then FET is in saturation mode.

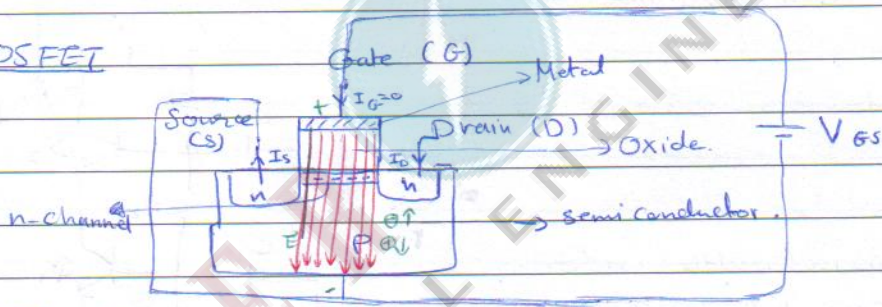
$V_{DS(sat)} = V_{GS} - V_{TN}$

FET Amplifiers:

Review : FET (field effect transistor)

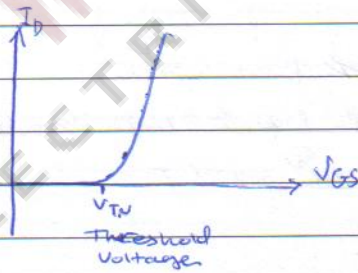
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nMOSFET

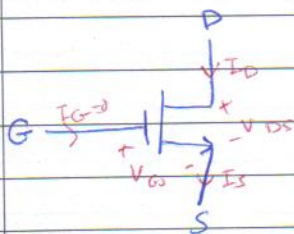


$\Rightarrow I_G = 0$

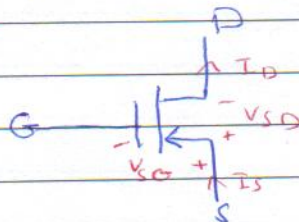
$\Rightarrow I_D = I_S$

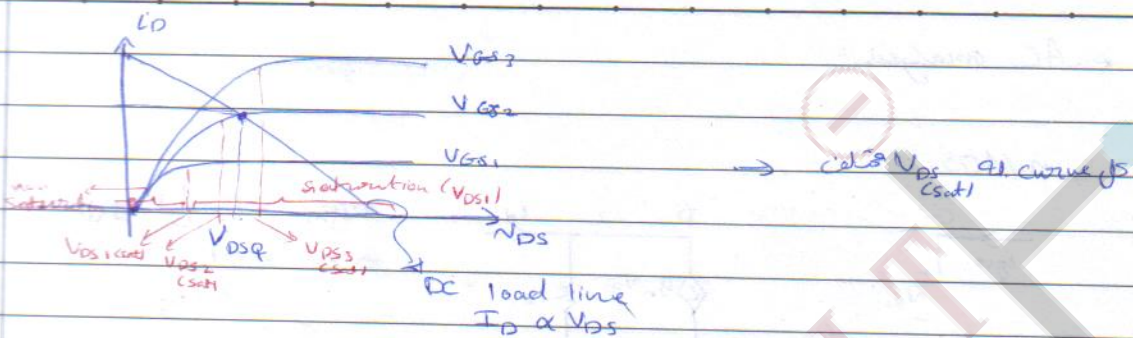


nMOSFET



pMOSFET





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$$\Rightarrow A_v(\text{BJT}) \gg A_v(\text{FET})$$

← DC analysis:

$$\Rightarrow I_G = 0$$

$$\Rightarrow I_D = I_S$$

$$\Rightarrow I_{DQ} = K_n (V_{GSQ} - V_{TN})^2$$

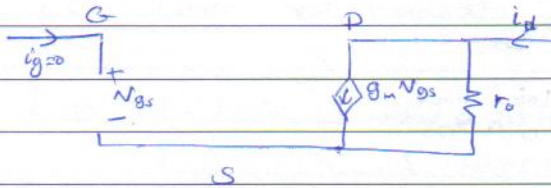
K_n : conduction parameter (mA/V^2)

⇒ FET to work as amplifier, it should be in saturation mode. If $V_{DS} > |V_{DS(\text{sat})}|$, then FET is in saturation mode.

$$V_{DS(\text{sat})} = V_{GS} - V_{TN}$$

* AC analysis :

nMOS

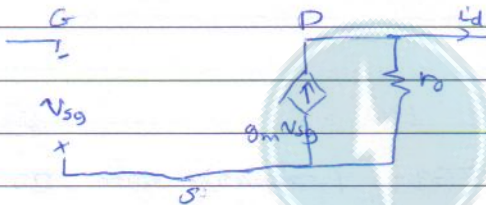


$$\Rightarrow g_m = 2K_n [V_{GSQ} - V_{TN}]$$

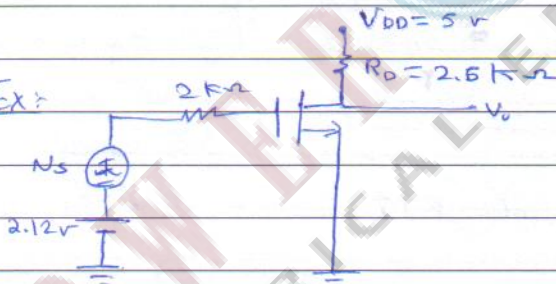
$$\Rightarrow r_o = \frac{1}{\lambda I_{DQ}}$$

λ : the channel length modulation parameter (Positive value) (V^{-1})

pMOS



Ex:



Common source amplifiers

$V_{TN} = 1V$, $k_n = 0.8 \text{ mA/V}^2$

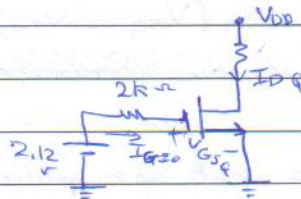
$\lambda = 0.02$

Final $A_v = \frac{v_o}{v_s}$?

DC analysis

Input loop :

$V_{GSQ} = 2.12V$



No. _____

$$\Rightarrow I_{DQ} = k_n (V_{GSQ} - V_{TN})^2$$
$$= 1 \text{ mA}$$

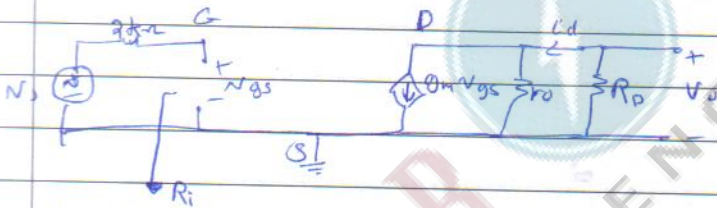
\Rightarrow Output loop

$$-5 + 2.5 I_{DQ} + V_{DSQ}$$
$$V_{DSQ} = 2.5 \text{ V}$$

$$\Rightarrow V_{DS(sat)} = V_{GSQ} - V_{TN} = 2.12 - 1 = 1.12 \text{ V}$$

$\therefore V_{DSQ} > V_{DS(sat)} \rightarrow$ saturation mode

* AC analysis:



$$A_v = \frac{V_o}{N_s}$$

$$V_o = -g_m V_{gs} (R_D \parallel r_o)$$

$$V_{gs} = N_s$$

$$\therefore A_v = -g_m (R_D \parallel r_o)$$

$$A_v = -4.26$$

phase shift between N_s and $V_o = 180^\circ$.

$$R_i = \infty$$

$$R_o = R_D \parallel r_o$$

$$g_m = 2k_n (V_{GSQ} - V_{TN})$$
$$= 1.679 \text{ mA/V}$$

$$r_o = \frac{1}{\lambda I_{DQ}} = 50 \text{ k}\Omega$$